

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None or Semi Std	
	5.0	Overall Thickness	405.00 +/- 6.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00	ADE to ASTM F657
	7.0	Bow	<60.00 μ m	ADE to ASTM F534, 20%
	8.0	Warp	<60.00 μ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	13.0	Handle Thickness	400.00 +/- 5.00 μ m	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.1~10 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and lasermarking	Wafer Vendor
	19.0	Handle Silicon Dislocation Etch Pit Density	<100/cm ²	Wafer Vendor.
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	2,000.00 +/- 200.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle Wafer	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	25.0	Nominal Thickness	5.00 +/- 1.00 μ m	FTIR, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phosphorous	Wafer Vendor
	29.0	Device Resistivity	0.4 ~ 1.0 Ohmcm	Wafer Vendor
	30.0	Voids	none	Bright Light, 100% (note 2)
	31.0	Scratches	Frontside none, backside soft handling marks	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)
	33.0	Dislocation Etch Pit Density	<100/cm ²	Wafer Vendor. SEMI MF1809 or ASTM F416-94

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information